## **Supplementary Information for**

## Effects of doping and planar defects on thermoelectric properties of InAs nanowires

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**Fig. S1** SEM images of (a) membrane-type MTMP with a Si-doped InAs NW with Ni/Al electrodes. (b) variations of I-V curves for undoped and Si-doped InAs NWs with temperature.



**Fig. S2** (a) high resolution TEM image and (b) HAADF image of Si-doped InAs NW. Yellow dotted lines indicate the interfaces between the ZB and WZ phases while red arrows denote stacking faults in the ZB phase.